

November 2013

## **FQP27N25**

# N-Channel QFET<sup>®</sup> MOSFET 250 V, 25.5 A, 110 m $\Omega$

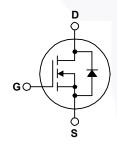
### **Description**

This N-Channel enhancement mode power MOSFET is produced using Fairchild Semiconductor's proprietary planar stripe and DMOS technology. This advanced MOSFET technology has been especially tailored to reduce on-state resistance, and to provide superior switching performance and high avalanche energy strength. These devices are suitable for switched mode power supplies, active power factor correction (PFC), and electronic lamp ballasts.

#### **Features**

- 25.5 A, 250 V,  $R_{DS(on)}$  = 110 m $\Omega$  (Max.) @  $V_{GS}$  = 10 V,  $I_D$  = 12.75 A
- Low Gate Charge (Typ. 50 nC)
- · Low Crss (Typ. 45 pF)
- · 100% Avalanche Tested





### Absolute Maximum Ratings T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter		FQP27N25	Unit
V <sub>DSS</sub>	Drain-Source Voltage		250	V
I <sub>D</sub>	Drain Current - Continuous (T <sub>C</sub> = 25°C	5)	25.5	Α
	- Continuous (T <sub>C</sub> = 100°	C)	16.2	А
I <sub>DM</sub>	Drain Current - Pulsed	(Note 1)	102	А
$V_{GSS}$	Gate-Source Voltage		± 30	V
E <sub>AS</sub>	Single Pulsed Avalanche Energy	(Note 2)	600	mJ
I <sub>AR</sub>	Avalanche Current	(Note 1)	25.5	Α
E <sub>AR</sub>	Repetitive Avalanche Energy	(Note 1)	18	mJ
dv/dt	Peak Diode Recovery dv/dt	(Note 3)	5.5	V/ns
$P_D$	Power Dissipation (T <sub>C</sub> = 25°C)		180	W
	- Derate above 25°C		1.43	W/°C
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Temperature Range		-55 to +150	°C
T <sub>L</sub>	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 seconds		300	°C

### **Thermal Characteristics**

Symbol	Parameter	FQP27N25	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	0.7	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

# **Package Marking and Ordering Information**

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FQP27N25	FQP27N25	TO-220	Tube	N/A	N/A	50 units

### **Electrical Characteristics**

T<sub>C</sub> = 25°C unless otherwise noted.

Symbol	Parameter	Test Conditions	Min	Тур	Max	Uni
Off Ch	- wasto visting					
	aracteristics	N 0 N 1 050 A		I		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$	250			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 $\mu$ A, Referenced to 25°C		0.29		V/°(
I <sub>DSS</sub>	Zoro Coto Voltago Droin Current	V <sub>DS</sub> = 250 V, V <sub>GS</sub> = 0 V	-		1	μΑ
	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 200 V, T <sub>C</sub> = 125°C			10	μΑ
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30 V, V <sub>DS</sub> = 0 V			100	nΑ
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse	V <sub>GS</sub> = -30 V, V <sub>DS</sub> = 0 V			-100	nΑ
On Cha	aracteristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 12.75 A	-	0.083	0.11	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 50 V, I <sub>D</sub> = 12.75 A		24		S
Dynam C <sub>iss</sub>	ic Characteristics Input Capacitance	V 05VV 0V		1900	2450	pF
C <sub>oss</sub>	Output Capacitance	$V_{DS} = 25 \text{ V}, V_{GS} = 0 \text{ V},$ f = 1.0 MHz		360	470	рF
C <sub>rss</sub>	Reverse Transfer Capacitance	1 - 1.0 MHZ		45	60	pF
	ing Characteristics					<u> </u>
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 125 V, I <sub>D</sub> = 27 A,		32	75	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25 \Omega$		270	550	ns
$t_{d(off)}$	Turn-Off Delay Time	(Note 4)		80	170	ns
t <sub>f</sub>	Turn-Off Fall Time			120	250	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 200 V, I <sub>D</sub> = 27 A,		50	65	nC
	Gate-Source Charge	V <sub>GS</sub> = 10 V		12.5		nC
$Q_{gs}$						

### **Drain-Source Diode Characteristics and Maximum Ratings**

I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current		 	25.5	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode F	orward Current	 /	102	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 25.5 A	 J/	1.5	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>S</sub> = 27 A,	 220		ns
Q <sub>rr</sub>	Reverse Recovery Charge	dI <sub>F</sub> / dt = 100 A/μs	 1.8		μС

- **Notes:**1. Repetitive Rating : Pulse width limited by maximum junction temperature. 2. L = 1.5 mH, I $_{AS}$  = 25.5 A, V $_{DD}$  = 50 V, R $_{G}$  = 25  $\Omega$ , starting T $_{J}$  = 25°C. 3. I $_{SD}$  ≤ 27 A, di/dt ≤ 300 A $\mu$ Is, V $_{DD}$  ≤ BV $_{DSS}$ , starting T $_{J}$  = 25°C. 4. Essentially independent of operating temperature.

## **Typical Characteristics**

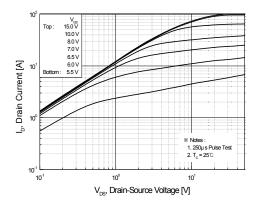
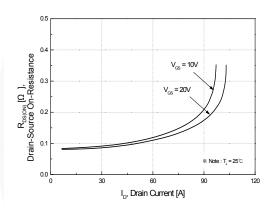


Figure 1. On-Region Characteristics

Figure 2. Transfer Characteristics



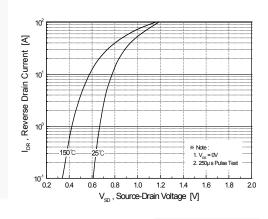
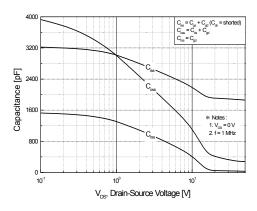


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature



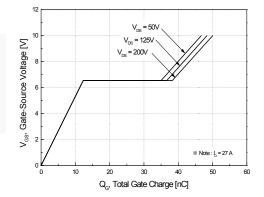


Figure 5. Capacitance Characteristics

Figure 6. Gate Charge Characteristics

## Typical Characteristics (continued)

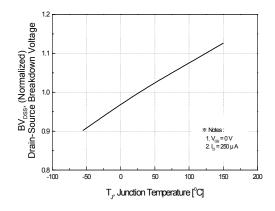
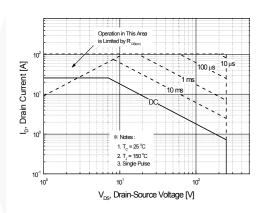


Figure 7. Breakdown Voltage Variation vs. Temperature

Figure 8. On-Resistance Variation vs. Temperature



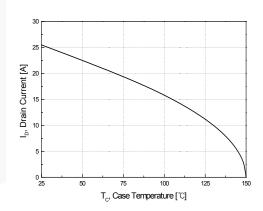


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature

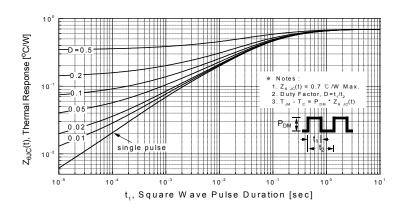


Figure 11. Transient Thermal Response Curve

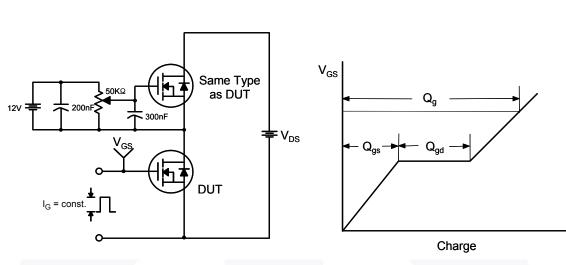


Figure 12. Gate Charge Test Circuit & Waveform

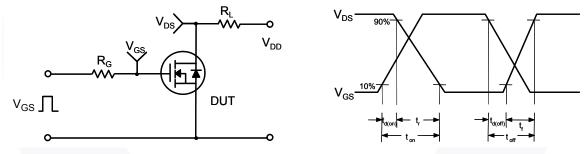


Figure 13. Resistive Switching Test Circuit & Waveforms

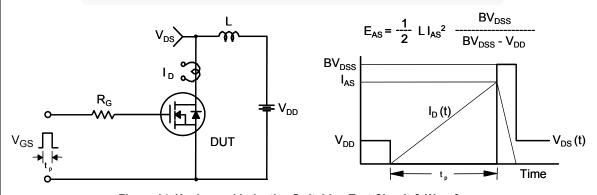
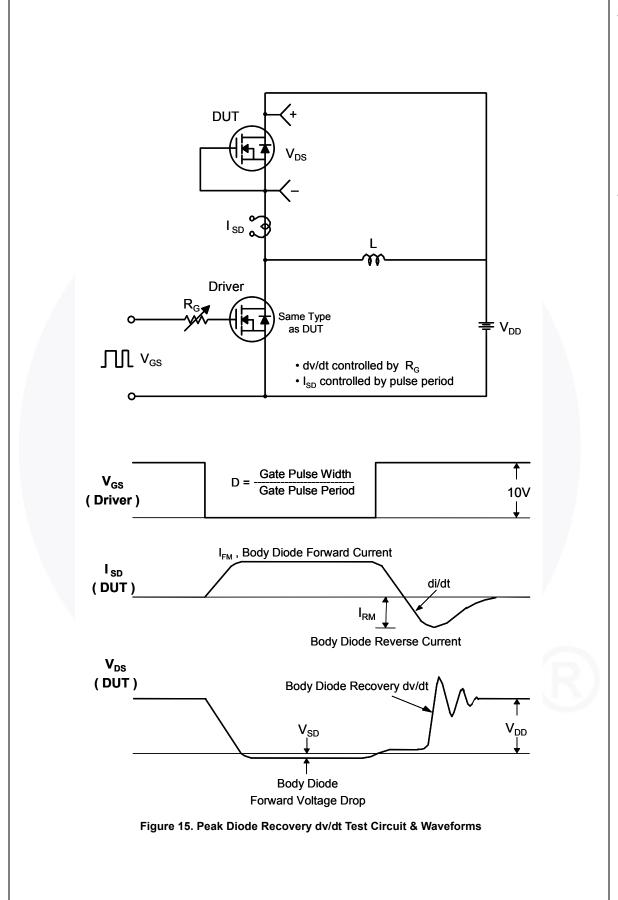


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



### **Mechanical Dimensions**

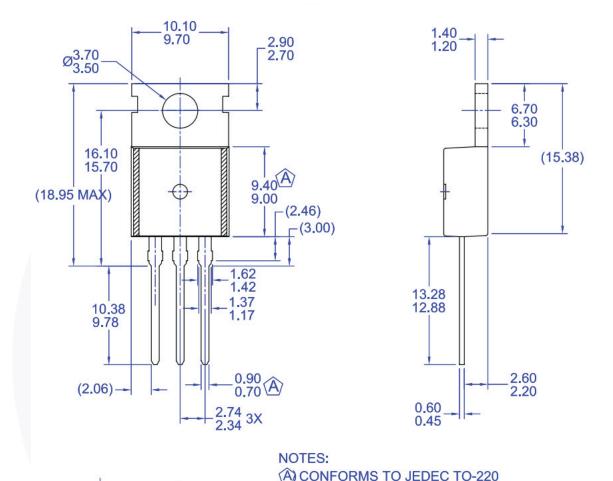


Figure 16. TO220, Molded, 3-Lead, Jedec Variation AB

VARIATION AB EXCEPT WHERE NOTED

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D) DRAWING FILE/REVISION: MKT-TO220Y03REV1

B) ALL DIMENSIONS ARE IN MILLIMETERS.

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